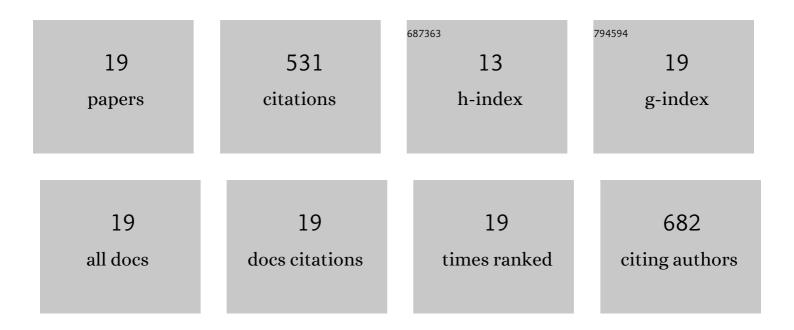
Yanbing Han

List of Publications by Year in descending order

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YANBING HAN

#	Article	IF	CITATIONS
1	Wide Band Gap Chalcogenide Semiconductors. Chemical Reviews, 2020, 120, 4007-4055.	47.7	246
2	Effects of silicon doping on the performance of tin oxide thin film transistors. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1010-1015.	1.8	36
3	Fabrication of 2D PdSe ₂ /3D CdTe Mixed-Dimensional van der Waals Heterojunction for Broadband Infrared Detection. ACS Applied Materials & Interfaces, 2021, 13, 41791-41801.	8.0	30
4	Optoelectronic Properties of Strontium and Barium Copper Sulfides Prepared by Combinatorial Sputtering. Chemistry of Materials, 2017, 29, 8239-8248.	6.7	28
5	Combinatorial Tuning of Structural and Optoelectronic Properties in Cu Zn1â^'S. Matter, 2019, 1, 862-880.	10.0	26
6	Characteristic of Bismuth-Doped Tin Oxide Thin-Film Transistors. IEEE Transactions on Electron Devices, 2016, 63, 1904-1909.	3.0	25
7	H2O adsorption on amorphous In-Ga-Zn-O thin-film transistors under negative bias stress. Applied Physics Letters, 2017, 111, .	3.3	23
8	Stabilization of wide band-gap p-type wurtzite MnTe thin films on amorphous substrates. Journal of Materials Chemistry C, 2018, 6, 6297-6304.	5.5	21
9	Influences of Nitrogen Doping on the Electrical Characteristics of Indium-Zinc-Oxide Thin Film Transistors. IEEE Transactions on Device and Materials Reliability, 2016, 16, 642-646.	2.0	16
10	H ₂ 0 Induced Hump Phenomenon in Capacitance–Voltage Measurements of a-IGZO Thin-Film Transistors. IEEE Transactions on Device and Materials Reliability, 2016, 16, 20-24.	2.0	16
11	Enhancing the optical absorption of chalcogenide perovskite BaZrS3 by optimizing the synthesis and post-processing conditions. Journal of Solid State Chemistry, 2022, 307, 122872.	2.9	15
12	Combinatorial Nitrogen Gradients in Sputtered Thin Films. ACS Combinatorial Science, 2018, 20, 436-442.	3.8	13
13	Zinc-Stabilized Manganese Telluride with Wurtzite Crystal Structure. Journal of Physical Chemistry C, 2018, 122, 18769-18775.	3.1	13
14	Effects of Nitrogen Doping on Performance of Amorphous SnSiO Thin Film Transistor. Journal of Display Technology, 2016, 12, 1560-1564.	1.2	10
15	Templated Growth of Metastable Polymorphs on Amorphous Substrates with Seed Layers. Physical Review Applied, 2020, 13, .	3.8	7
16	Asymmetric contact in tin bismuth oxide thin film transistors. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600589.	1.8	2
17	Wurtzite materials in alloys of rock salt compounds. Journal of Materials Research, 2020, 35, 972-980.	2.6	2
18	High-throughput fabrication and semi-automated characterization of oxide thin film transistors. Chinese Physics B, 2020, 29, 018502.	1.4	1

#	Article	IF	CITATIONS
19	Solution processed amorphous gallium-incorporated tin oxide thin-film transistors. Japanese Journal of Applied Physics, 2020, 59, 050906.	1.5	1